

# (19) United States

## (12) Patent Application Publication (10) Pub. No.: US 2023/0230938 A1 Verma et al.

(43) **Pub. Date:** 

Jul. 20, 2023

### (54) METHOD FOR FABRICATING AN INTEGRATED CIRCUIT DEVICE

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(21) Appl. No.: 18/123,317

(22) Filed: Mar. 19, 2023

## Related U.S. Application Data

(60) Division of application No. 17/402,633, filed on Aug. 16, 2021, now Pat. No. 11,637,080, which is a continuation of application No. 16/886,721, filed on May 28, 2020, now Pat. No. 11,127,700.

#### **Publication Classification**

(51) Int. Cl. H01L 23/58 (2006.01)H01L 21/71 (2006.01)H01L 21/56 (2006.01)

(52)U.S. Cl.

H01L 23/585 (2013.01); H01L 21/71 CPC ..... (2013.01); H01L 21/56 (2013.01)

#### (57)ABSTRACT

A method for fabricating an integrated circuit device is disclosed. A substrate is provided and an integrated circuit area is formed on the substrate. The integrated circuit area includes a dielectric stack. A seal ring is formed in the dielectric stack and around a periphery of the integrated circuit area. A trench is formed around the seal ring and exposing a sidewall of the dielectric stack. The trench is formed within a scribe line. A moisture blocking layer is formed on the sidewall of the dielectric stack, thereby sealing a boundary between two adjacent dielectric films in the dielectric stack.

